# Solutions of

# **Electronics Engineering** $\mathbf{FATE} = \mathbf{2016}$

Session 1 | Set-1



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# **GATE 2016 : Solutions**

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Mr. B. Singh

(Ex. IES) CMD, MADE EASY Group

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	One Mark (	Questions
Q.1	<ul> <li>.1 Which of the following is CORRECT with respect to grammar and u Mount Everest is</li> <li>(a) the highest peak in the world</li> <li>(b) highest peak in the world</li> <li>(c) one of highest peak in the world</li> <li>(d) one of the highest peak in the world</li> </ul>	
Ans.	(a)	• • • End of Solution
Q.2	The policeman asked the victim of (a) loose (c) loss	f a theft, "What did you? (b) lose (d) louse
Ans.	(b)	
Q.3	Despite the new medicine's in treating diabetes, it is not widely         (a) effectiveness - prescribed       (b) availability - used         (c) prescription - available       (d) acceptance - proscribed	
Ans.	(a)	
<b>Q</b> .4	are unripe fruits. Of the unripe fru	<ul> <li>End of Solution</li> <li>and unripe mixed together, 15%</li> <li>uits, 45% are apples. Of the ripe ones, 66%</li> <li>total of 5692000 fruits, how many of them</li> <li>(b) 2467482</li> </ul>
	(c) 2789080	(d) 3577422
Ans.	(a)	(d) 3577422

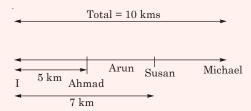
MADE EASY India's Best Institute for IES, GATE & PSUs Q.5 Michael lives 10 km away from where I live. Ahmed lives 5 km away and Susan lives 7 km away from where I live. Arun is farther away than Ahmed but closer than Susan from where I live. From the information provided here, what is one possible distance (in km) at which I live from Arun's place?

(a)	3.00	(b)	4.99
(c)	6.02	(d)	7.01

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#### Ans. (c)

Following line with respective distances can be drawn



Arun can reside anywhere between Ahmed and Susan i.e. between 5 km and 7 km from I.

5 < 6.02 < 7

#### **Two Marks Questions**

**Q.6.** A person moving through a tuberculosis prone zone has a 50% probability of becoming infected. However, only 30% of infected people develop the disease. What percentage of people moving through a tuberculosis prone zone remains infected but does not show symptoms of disease?

(a)	15	(b)	33
(c)	35	(d)	37

Ans. (c)

The required probability

$$0.5 \times 0.7 = 0.35 \approx \frac{35}{100} = 35\%$$

End of Solution

End of Solution

- Q.7 In a world filled with uncertainty, he was glad to have many good friends. He has always assisted them in times of need and was confident that they would reciprocate. However, the events of the last week proved him wrong. Which of the following inference(s) is/are logically valid and can be inferred from the above passage?
  - I. His friends were always asking him to help them.
  - II. He felt that when in need of help, his friends would let him down.
  - III. He was sure that his friends would help him when in need.
  - IV. His friends did not help him last week.



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Leela. When Pavithra and Shiva are Pavithra wins more often than Lee Which one of the following stateme	ents must be TRUE based on the above? Leela and Pavithra, he often loses. an Pavithra. e three. ara) • • • End of Solution
<ul> <li>b)</li> <li>Leela is older than her cousin Pavit Leela. When Pavithra and Shiva are Pavithra wins more often than Lee Pavithra wins more often than Lee Which one of the following statements a) When Shiva plays chess with I b) Leela is the oldest of three.</li> <li>c) Shiva is better chess player that d) Pavithra is the youngest of the d)</li> <li>L &gt; P (Leela is older thean Pavith S &gt; L (Shiv is older than Leela)</li> <li>So Pavithra is youngest</li> </ul>	End of Solution The second structure of the
Leela is older than her cousin Pavit Leela. When Pavithra and Shiva are Pavithra wins more often than Lee Which one of the following stateme a) When Shiva plays chess with I b) Leela is the oldest of three. c) Shiva is better chess player that d) Pavithra is the youngest of the d) L > P (Leela is older thean Pavith S > L (Shiv is older than Leela) So Pavithra is youngest	chra, Pavithra's brother Shiva is older than e visiting Leela, all there like to play chess. ela does. ents must be TRUE based on the above? Leela and Pavithra, he often loses. an Pavithra. e three. ara)
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L > P (Leela is older thean Pavith S > L (Shiv is older than Leela) So Pavithra is youngest	• • End of Solution
S > L (Shiv is older than Leela) So Pavithra is youngest	• • End of Solution
o Pavithra is youngest	
f $q^{-a} = rac{1}{r}$ and $r^{-b} = rac{1}{s}$ and $s^{-c} =$	
a) $(rqs)^{-1}$ c) 1	$\frac{1}{q}$ , the value of <i>abc</i> is (b) 0 (d) $r + q + s$
c)	
	$\mathbf{r} = \mathbf{r}, \mathbf{r}^{\mathbf{b}} = \mathbf{s}, \mathbf{s}^{\mathbf{c}} = \mathbf{q}$
-	$= \log r,$
	$r = \log s$ ,
-	$= \log q$
	$= \frac{\log r}{\log q} \times \frac{\log s}{\log r} \times \frac{\log q}{\log s} = 1$
	• • End of Solution
lone for 12 hours a day. <i>R</i> can fin 2 hours per day. <i>Q</i> worked 12 hour	<ul> <li>act. Q can finish the task in 25 days, working alone for the task in 50 days, working alone for the sa day but took sick leave in the beginning day on all days. What is the ratio of work in the start of the projects?</li> <li>(b) 11:10</li> </ul>
	$q^a$ $a \cdot \log q$ $b \cdot \log r$ $c \cdot \log s$ $c \in \log s$ c

Ans. (c)

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Q can do work in  $25 \times 12 = 300$  hrs

R can do work in 50 × 12 = 600 hrs

E

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So we can say Q is twice efficient as R

Now Q worked only for 5 days at a rate of 12 hrs/day. So for 60 units of his

work (Total work for Q i.e. 300 hrs) he will do only  $\frac{1}{5}$  of work  $\left(\frac{60}{300} = \frac{1}{5}\right)$ 

While R worked for all 7 days at a rate of 18 hrs/day

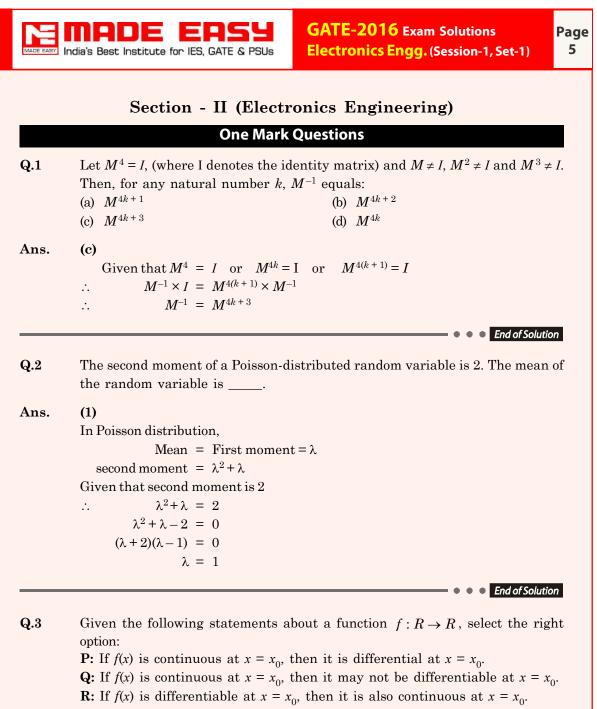
So he will do  $18 \times 7 = 126$  of his work (Total work for 600 hrs)

He will do  $\left(\frac{126}{600} = 0.21\right)$  of his work

So required ratio  $\left(\frac{1}{5}:\frac{126}{600}\right)$  = 120 : 126

20:21

End of Solution

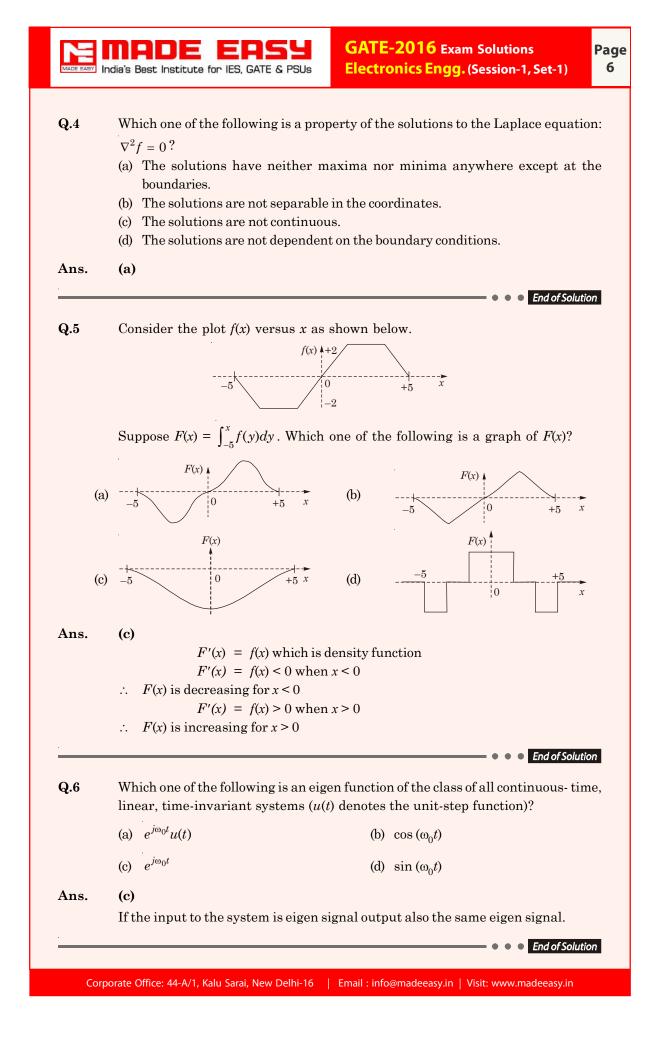


- (a) P is true, Q is false, R is false
- (b) P is false, Q is true, R is true
- (c) P is false, Q is true, R is false
- (d) P is true, Q is false, R is true

#### Ans. (b)

P: If f(x) is continuous at  $x = x_0$ , then it is also differentiable at  $x = x_0$ Q: If f(x) is continuous at  $x = x_0$ , then it may or may not be derivable at  $x = x_0$ R: If f(x) is differentiable at  $x = x_0$ , then it is also continuous at  $x = x_0$ P is falseQ is trueR is trueOption (b) is correct

End of Solution



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<b>Q.7</b> A continuous time function $x(t)$ is periodic with period $T$ . The function is saturiformly with a sampling period $T_s$ . In which one of the following cases sampled signal periodic?		
	(a) $T = \sqrt{2}T_s$	(b) $T = 1.2 T_s$
	(c) Always	(d) Never
Ans.	(b)	
	A signal is said to be periodic if $\frac{T}{T}$	- is a rational number.
	Here, $T = 1.2 T_s$	
		hich is a rational number
<b>Q</b> .8		$[n] + b^n u[n]$ , where $u[n]$ denotes the unit-step region of convergence (ROC) of the z-transform (b) $ z  >  b $ (d) $ a  <  z  <  b $
Ans.	(b)	
	Given, x	$n] = a^n u[n] + b^n u[n]$
	Also given,	0 <  a  <  b  < 1 0 = ( z  >  a )  and  ( z  >  b )
		$\mathbf{C} =  z  >  b $
Q.9	Consider a two-port network with the transmission matrix : $T = \begin{bmatrix} A & B \\ C & D \end{bmatrix}$ . If the network is reciprocal, then	
	(a) $T^{-1} = T$ (c) Determinant $(T) = 0$	<ul> <li>(b) T<sup>2</sup> = T</li> <li>(d) Determinant (T) = 1</li> </ul>
Ans.	(d) For reciprocal network $AD - BC =$  T  = 1	
Q.10	impulse train of frequency 46 Hz.	• • End of Solution uency 33 Hz is multiplied with a periodic Dirac The resulting signal is passed through an ideal frequency of 23 Hz. The fundamental frequency





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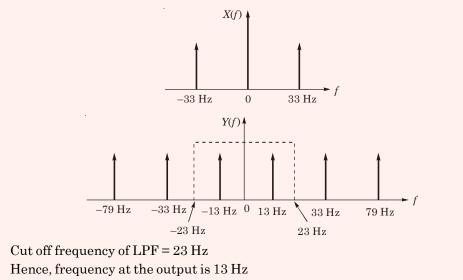
Ans. (13)

If x(t) is a message signal and y(t) is a sampled signal, then y(t) is related to x(t) as

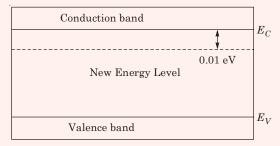
$$y(t) = x(t) \sum_{n = -\infty}^{\infty} \delta(t - nT_s)$$
$$Y(f) = f_s \sum_{n = -\infty}^{\infty} X(f - nf_s)$$

Spectrum of X(f) and Y(f) are as shown

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**Q.11** A small percentage of impurity is added to an intrinsic semiconductor at 300 K. Which one of the following statements is true for the energy band diagram shown in the following figure?



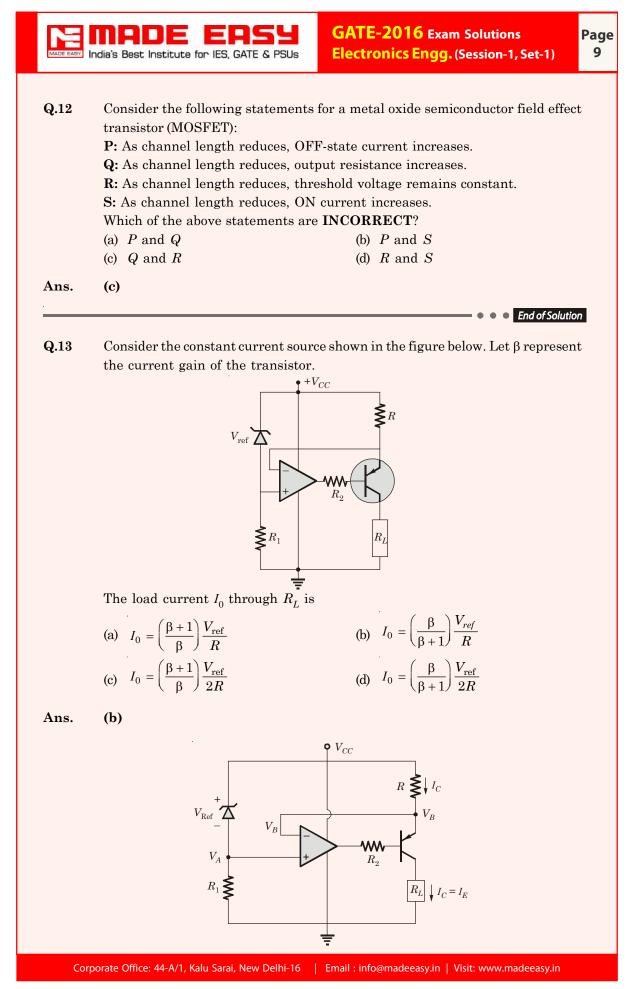
- (a) Intrinsic semiconductor doped with pentavalent atoms to form n-type semiconductor
- (b) Intrinsic semiconductor doped with trivalent atoms to form n-type semiconductor
- (c) Intrinsic semiconductor doped with pentavalent atoms to form p-type semiconductor
- (d) Intrinsic semiconductor doped with trivalent atoms to form p-type semiconductor

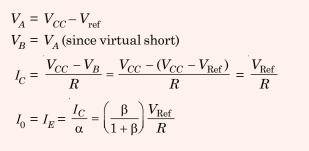
Ans. (a)

Pentavalent impurity when introduced in Intrinsic SC, a new discrete energy level called Donor energy level is created just below the conduction band.



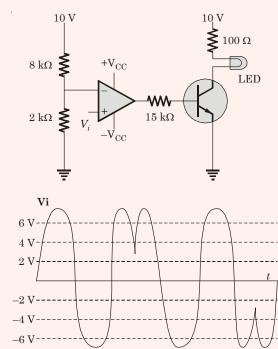
End of Solution





End of Solution

**Q.14** The following signal  $V_i$  of peak voltage 8 V applied to the non-inverting terminal of an ideal opamp. The transistor has  $V_{BE} = 0.7 \text{ V}$ ,  $\beta = 100$ ;  $V_{LED} = 1.5 \text{ V}$ ,  $V_{CC} = 10 \text{ V}$  and  $-V_{CC} = -10 \text{ V}$ 



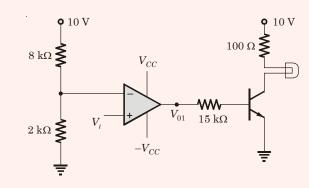
The number of times the LED glows is\_\_\_\_

Ans. (3)

IADE

EA

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End of Solution

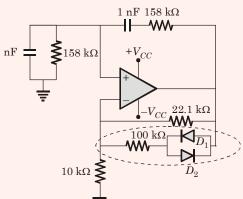
$$V_B = \frac{10\,\mathrm{V} \times 2\,\mathrm{K}}{8\,\mathrm{K} + 2\,\mathrm{K}} = 2\,\mathrm{V}$$

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When  $V_1$  exceeds 2 V output of opamp  $V_{01}$  goes to  $V_{CC}$  and drives BJT into saturation shorted LED will glow,

In the given problem  $V_i$  exceeds 2V three times and hence output  $V_{01}$  of opamp goes to  $V_{CC}$  thrice so that LED glow three times.

 $\textbf{Q.15} \qquad \text{Consider the oscillator circuit shown in the figure. The function of the network} \\ \text{(shown in dotted lines) consisting of the 100 k} \Omega \text{ resistor in series with the two} \\ \text{diodes connected back-to-back is to:} \end{cases}$ 



- (a) introduce amplitude stabilization by preventing the op amp from saturating and thus producing sinusoidal oscillations of fixed amplitude
- (b) introduce amplitude stabilization by forcing the opamp to swing between positive and negative saturation and thus producing square wave oscillations of fixed amplitude
- (c) introduce frequency stabilization by forcing the circuit to oscillate at a single frequency
- (d) enable the loop gain to take on a value that produces square wave oscillations

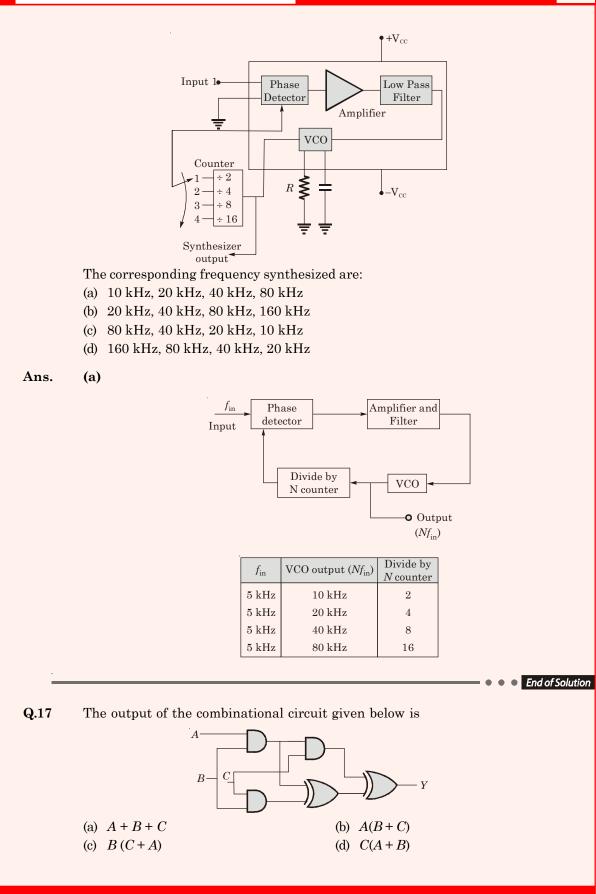
#### Ans. (a)

The given circuit is Wein-bridge oscillator which produced sinusoidal oscillations and the amplitude of output wave is decided by feedback through inverting input terminal of opamp.

#### End of Solution

Q.16 The block diagram of a frequency synthesizer consisting of a Phase Locked Loop (PLL) and a divide-by-N counter (comprising ÷ 2, ÷ 4, ÷ 8, ÷ 16 outputs) is sketched below. The synthesizer is excited with a 5 kHz signal (Input 1). The free-running frequency of the PLL is set to 20 kHz. Assume that the commutator switch makes contacts repeatedly in the order 1 - 2 - 3 - 4.





Ans. (c)

**Q.18** 

Ans.

Q.19

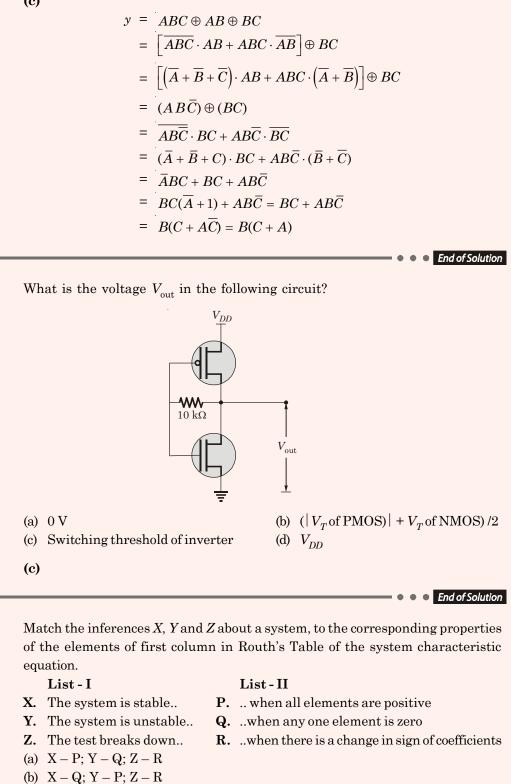
(c) X - R; Y - Q; Z - P(d) X - P; Y - R; Z - Q

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Ans.	When all elements are positive, the system is stable. When any element is zer test breaks down. When there is change in sign of coefficients, the system is uns		
Q.20	<ul> <li>A closed-loop control system is stable if the Nyquist plot of the corresponding open-loop transfer function</li> <li>(a) encircles the <i>s</i>-plane point (-1 + <i>j</i>0) in the counterclockwise direction as many times as the number of right-half <i>s</i>-plane poles.</li> <li>(b) encircles the <i>s</i>-plane point (0 - <i>j</i>1) in the clockwise direction as many times as the number of right-half <i>s</i>-plane poles.</li> <li>(c) encircles the <i>s</i>-plane point (-1 + <i>j</i>0) in the counterclockwise direction as many times as the number of left-half <i>s</i>-plane poles.</li> <li>(d) encircles the <i>s</i>-plane point (-1 + <i>j</i>0) in the counterclockwise direction as many times as the number of right-half <i>s</i>-plane poles.</li> </ul>		
Ans.	(a) $N = P - Z$ $N = \text{Number of encirclements of } (-1+j0). \text{ It is positive if nyquist plot}$ $\text{encircles the point } -1+j0 \text{ in counterclockwise direction.}$ $Z = \text{Number of closed loop poles lying in the right half of s-plane}$ $P = \text{Number of open loop poles lying in right half of s-plane}$ For stability $Z = 0 \Rightarrow N = P$ $\text{End of Solution}$		
Q.21	Consider the binary data transmission at a rate of 56 kbps using baseband binary pulse amplitude modulation (PAM) that is designed to have a raised-cosine spectrum. The transmission bandwidth (in kHz) required of a roll-off factor of 0.25 is		
Ans.	(35) Bit rate, $R_b = 56$ kbps Roll-off factor, $\alpha = 0.25$ Transmission BW $= \frac{R_b}{2}(1 + \alpha)$ $= \frac{56}{2}(1.25) = 28 \times 1.25 = 35$ kHz		
Q.22	A superheterodyne receiver operates in the frequency range of 58 MHz – 68 MHz. The intermediate frequency $f_{\rm IF}$ and local oscillator frequency $f_{\rm LO}$ are chosen such that $f_{\rm IF} \leq f_{\rm LO}$ . It is required that the image frequencies fall outside the 58 MHz – 68 MHz band. The minimum required $f_{\rm IF}$ (in MHz) is		

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Ans.	(5)
	$f_s = 58  \mathrm{MHz} - 68  \mathrm{MHz}$
	$f_{si}$ should fall outside the range $58{ m MHz}$ - $68{ m MHz}$
	Hence $f_{s\min} = 58 \text{ MHz}$
	$f_{\rm si} = f_s + 2IF > 68 { m MHz}$
	58  MHz + 2IF > 68  MHz
	$IF > 5 \mathrm{MHz}$
	$\Rightarrow$ ( <i>IF</i> ) <sub>min</sub> = 5 MHz
	• • End of Solution
Q.23	The amplitude of a sinusoidal carrier is modulated by a single sinusoid to obtain the amplitude modulated signal $s(t) = 5 \cos 1600\pi t + 20 \cos 1800\pi t + 5 \cos 2000\pi t$ . The value of the modulation index is
Ans.	(0.5)
	$s(t) = 5\cos 1600 \pi t + 20\cos 1800 \pi t + 5\cos 2000 \pi t$ $s(t) = 20\cos 1800 \pi t + 5\cos 1600 \pi t + 5\cos 2000 \pi t$
	$s(t) = A_c \cos 2\pi f_c t + \frac{A_c \mu}{2} \cos 2\pi (f_c - f_m) t + \frac{A_c \mu}{2} \cos 2\pi (f_c + f_m) t$
	comparing, we get
	$A_c = 20 \text{ V}; \frac{A_c \mu}{2} = 5 \text{ V}$
	$\mu = \frac{10}{20} = 0.5$
	• • • End of Solution
Q.24	Concentric spherical shells of radii 2 m, 4 m, and 8 m carry uniform surface charge densities of 20 nC/m <sup>2</sup> , -4 nC/m <sup>2</sup> and $\rho_s$ , respectively. The value of
	$\rho_s(nC/m^2)$ required to ensure that the electric flux density $\vec{D} = \vec{0}$ at radius
	10 m is
Ans.	(-0.25)
	$\oint D \cdot ds = Q$ (charge enclosed)
	$Q_1 + Q_2 + Q_3 = 0$
	For $D = 0$
	$\rho_{s1}$ . $4\pi 2^2$ + $\rho_{s2}$ . $4\pi$ . $4^2$ + $\rho_{s3}$ . $4\pi$ . $8^2$ = $Q$ = $0$
	$20 \cdot 4 - 4.4^2 + \rho_{s3}. \ \delta^2 = 0$
	$80 - 64 + \rho_{s3} \cdot 8^2 = 0$
	$\rho_{s3} = \frac{-16}{64} = -0.25 \text{ nC/m}^2$

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The propagation constant of a lossy transmission line is (2 + j5) m<sup>-1</sup> and its Q.25 characteristic impedance is  $(50 + i0)\Omega$  at  $\omega = 10^6$  rad  $s^{-1}$ . The value of the line constants L, C, R, G are respectively,

(a) 
$$L = 200 \ \mu\text{H/m}, C = 0.1 \ \mu\text{F/m},$$

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- (b)  $L = 250 \,\mu\text{H/m}, C = 0.1 \,\mu\text{F/m},$  $R = 100 \ \Omega/m, G = 0.04 \ S/m$
- $R = 50 \ \Omega/m, G = 0.02 \ S/m$ (c)  $L = 200 \ \mu\text{H/m}, C = 0.2 \ \mu\text{F/m},$  $R = 100 \ \Omega/m, G = 0.02 \ S/m$ 
  - (d)  $L = 250 \,\mu\text{H/m}, C = 0.2 \,\mu\text{F/m},$  $R = 50 \ \Omega/m, G = 0.04 \ S/m$

**(b)** Ans.

$$\begin{split} \gamma &= \sqrt{(R+j\omega L)(G+j\omega C)} \\ Z_0 &= \sqrt{\frac{R+j\omega L}{G+j\omega C}} \\ \gamma \cdot Z_0 &= R+j\omega L = (2+j5) \ (50+j0) = 100+j250 \\ R &= 100 \ \Omega/m \\ L &= \frac{250}{\omega} = \frac{250}{10^6} = 250 \ \mu\text{H/m} \\ \frac{\gamma}{Z_0} &= \frac{2+j5}{50} = G+j\omega C = 0.04+j \ 0.1 \\ G &= 0.04 \ \text{S/m} \end{split}$$

$$C = \frac{0.1}{\omega} = \frac{0.1}{10^6} = 0.1 \ \mu\text{F/m}$$

End of Solution

#### **Two Marks Questions**

The integral  $\frac{1}{2\pi} \iint_D (x+y+10) dx, dy$ , where D denotes the disc:  $x^2 + y^2 \le 4$ , Q.26 evaluates to \_\_\_\_ Ans. (20) Put  $x = r\cos\theta$  $y = r\sin\theta$  $dxdy = rdrd\theta$  $= \frac{1}{2\pi} \int_{0}^{2\pi} \int_{0}^{2} (r(\cos\theta + \sin\theta) + 10)r \, dr d\theta$  $= \frac{1}{2\pi} \int_{0}^{2\pi} \int_{0}^{2\pi} (r^2(\cos\theta + \sin\theta) + 10r) dr d\theta$ Corporate Office: 44-A/1, Kalu Sarai, New Delhi-16 | Email : info@madeeasy.in | Visit: www.madeeasy.in

$$\begin{aligned} &= \frac{1}{2\pi} \left( \sum_{0}^{2\pi} (\cos\theta + \sin\theta) \left( \frac{r^3}{3} \right) \right)_{0}^{2} d\theta + 10 \int_{0}^{2\pi} \left( \frac{r^2}{2} \right) \right)_{0}^{2} d\theta \right) \\ &= \frac{1}{2\pi} \left\{ \frac{8}{5} \left( \cos\theta + \sin\theta \right) d\theta + \frac{1}{2\pi} \int_{0}^{2\pi} 5 \cdot (4) d\theta \right. \\ &= \frac{1}{2\pi} \left[ \frac{8}{3} \left( \sin\theta - \cos\theta \right) \right]_{0}^{2\pi} + \frac{1}{2\pi} \cdot 20(2\pi) \\ &= \frac{1}{2\pi} \left( \frac{8}{3} \left( 0 - 1 \right) - (0 - 1) + 20 \right) = 0 + 20 = 20 \end{aligned}$$

$$\begin{aligned} \textbf{Q.27} \qquad \textbf{A sequence } x[n] \text{ is specified as} \\ \left[ \frac{x[n]}{x[n-1]} \right] = \left[ \frac{1}{1} \cdot 0 \right]_{0}^{2\pi} \left[ \frac{1}{0} \right], \text{ for } n \geq 2. \end{aligned}$$

$$The initial conditions are  $x[0] = 1, x[1] = 1, \text{ and } x[n] = 0 \text{ for } n < 0. \text{ The value of } x[12] \text{ is } \underline{1} \\ \text{or } x[12] \text{ is } \underline{1} \\ \textbf{Ans.} \qquad (233) \end{aligned}$ 

$$\textbf{For} \qquad A = \left[ \frac{1}{1} \cdot \frac{1}{0} \right] \\ equation \qquad \left[ \frac{1-\lambda}{1} \cdot \frac{1}{-\lambda} \right] = 0 \\ \lambda^{2} - \lambda - 1 = 0 \\ \lambda^{2} - \lambda - 1 = 0 \\ \textbf{By Cayley Hamilton Theorem} \end{aligned}$$

$$\begin{aligned} A^{2} = A + I \\ A^{4} = A^{2} + 2A + I \\ = 8A^{4} + 2A + I \\ = 9(A + 1) + 12A + 4I \\ = 21A + 13I \\ A^{12} = A^{4} \cdot A^{2} = 14AA + 89I \\ = \left[ \frac{233}{3} \cdot 144 \\ 144 \quad 89 \right] \\ \left[ \frac{x[12]}{x[11]} \right] = \left[ \frac{233}{23} \cdot 144 \\ 144 \quad 89I \\ = \left[ \frac{x[12]}{233} \cdot 144 \\ 144 \quad 89I \\ x[12] = 233 \end{aligned}$$$$

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**Q.28** In the following integral, the contour C encloses the points  $2\pi j$  and  $-2\pi j$ 

$$-rac{1}{2\pi}\oint_Crac{\sin z}{\left(z-2\pi j
ight)^3}dz$$

The value of the integral is \_\_\_\_\_

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Ans. (-133.87)

$$I = -\frac{1}{2\pi} \int_{c} \frac{\sin z}{(z - 2\pi j)^{3}} dz$$
$$= -\frac{1}{2\pi} \times \frac{2\pi j f''(2\pi j)}{2!}$$
$$f(z) = \sin z$$
$$f'(z) = \cos z$$
$$f''(z) = -\sin z$$
$$I = -\frac{1}{2\pi} \times 2\pi j \frac{-\sin(2\pi j)}{2}$$
$$= -\frac{1}{2} \sinh 2\pi = -133.87$$

End of Solution

**Q.29** The region specified by  $\{(\rho, \phi, z): 3 \le \rho \le 5, \frac{\pi}{8} \le \phi \le \frac{\pi}{4}, 3 \le z \le 4.5\}$  in cylindrical coordinates has volume of \_\_\_\_\_.

Ans. (4.712)

$$V = \int_{\rho=3}^{5} \int_{\phi=\frac{\pi}{8}}^{\pi/4} \int_{z=3}^{4.5} \rho d\rho \, d\phi \, dz = \int_{3}^{4.5} \int_{\pi/8}^{\pi/4} \left(\frac{\rho^2}{2}\right) \Big|_{3}^{5} d\phi \, dz$$
$$= \int_{3}^{4.5} \int_{\pi/8}^{\pi/4} 8 \cdot d\phi \, dz = 8\phi \Big|_{\pi/8}^{\pi/4} \cdot z \Big|_{3}^{4.5}$$
$$= 8 \left(\frac{\pi}{4} - \frac{\pi}{8}\right) (4.5 - 3) = 8 \cdot \frac{\pi}{8} \cdot (1.5)$$
$$= 4.712$$

End of Solution

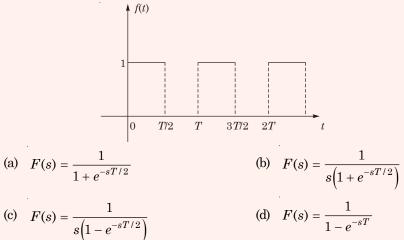
End of Solution

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**Q.30** The Laplace transform of the causal periodic square wave of period *T* shown in the figure below is

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Ans. (b)

$$\begin{split} L(f(t)) &= \left. \frac{1}{1 - e^{-sT}} \int_{0}^{T/2} e^{-st} dt \right. = \left. \frac{1}{1 - e^{-sT}} \left( \frac{e^{-st}}{-s} \right) \right|_{0}^{T/2} \\ &= \left. \frac{1}{s \left( 1 - e^{-sT} \right)} \cdot \left( 1 - e^{-sT/2} \right) \right. = \left. \frac{1}{s} \cdot \frac{1 - e^{-sT/2}}{\left( 1 - e^{-sT/2} \right) \left( 1 + e^{-sT/2} \right)} \\ &= \left. \frac{1}{s} \cdot \frac{1}{1 + e^{-sT/2}} \right. \end{split}$$

**Q.31** A network consisting of a finite number of linear resistor (R), inducer (L), and capacitor (C) elements, connected all in series or all in parallel, is excited with a source of the form

$$\sum_{k=1}^{3} a_k \cos(k\omega_0 t), \text{ where } a_k \neq 0, \ \omega_0 \neq 0.$$

The source has nonzero impedance. Which one of the following is a possible form of the output measured across a resistor in the network?

(a) 
$$\sum_{k=1}^{3} b_k \cos(k\omega_0 t + \phi_k), \text{ where } b_k \neq a_k, \forall k$$
  
(b) 
$$\sum_{k=1}^{3} b_k \cos(k\omega_0 t + \phi_k), \text{ where } b_k \neq 0, \forall k$$
  
(c) 
$$\sum_{k=1}^{3} a_k \cos(k\omega_0 t + \phi_k)$$
  
(d) 
$$\sum_{k=1}^{2} a_k \cos(k\omega_0 t + \phi_k)$$

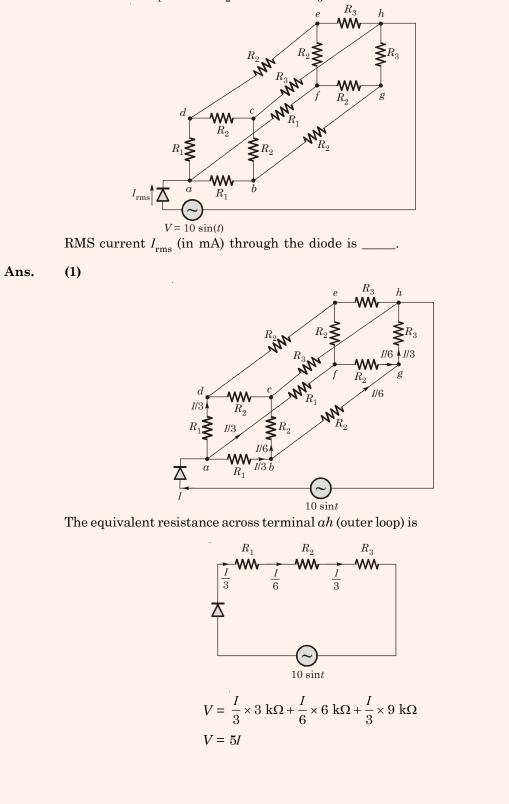
k=1

**Q.33** An AC voltage source  $V = 10 \sin(t)$  volts is applied to the following network. Assume that  $R_1 = 3 \text{ k}\Omega$ ,  $R_2 = 6 \text{ k}\Omega$  and  $R_3 = 9 \text{ k}\Omega$ , and that the diode is ideal.

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or

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For half wave rectifier

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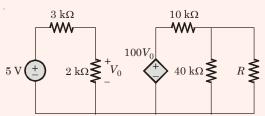
$$I_{\rm rms} = \frac{I_m}{(2)} = \frac{10 \sin t}{5 \,\mathrm{k}\Omega} = 2 \,\mathrm{sint} \,\mathrm{mA}$$
$$I_{\rm rms} = \frac{I_m}{2} = 1 \,\mathrm{mA}$$

 $\frac{V}{I} = 5 \text{ k}\Omega$ 

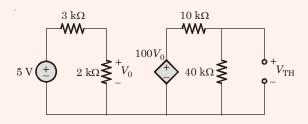
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End of Solution

**Q.34** In the circuit shown in the figure, the maximum power (in watt) delivered to the resistor *R* is \_\_\_\_\_



Ans. (0.8)



For maximum power transfer,

$$R = R_{TH}$$
$$V_0 = 5 \times \frac{2 \text{ k}\Omega}{5 \text{ k}\Omega} = 2 \text{ V}$$

From output loop,  $V_{\rm TH} = 100 \times 2 \times \frac{40 \text{ k}\Omega}{50 \text{ k}\Omega}$ 

$$V_{\rm TH} = 160 \, \rm V$$

and

÷.

$$R_{\rm TH} = 10 \text{ k}\Omega \mid \mid 40 \text{ k}\Omega = \frac{10 \times 40}{50} = 8 \text{ k}\Omega$$

Maximum power = 
$$\frac{V_{TH}^2}{4R_{TH}} = \frac{16 \times 16}{4 \times 8} = 0.8 \text{ W}$$

End of Solution

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Q.35 Consider the signal

$$\begin{split} x[n] &= 6\delta[n+2] + 3\delta[n+1] + 8\delta[n] + 7\delta[n-1] + 4\delta[n-2]. \\ \text{If } X(e^{j\omega}) \text{ is the discrete-time Fourier transform of } x[n], \\ \text{then } \frac{1}{\pi} \int_{-\pi}^{\pi} X(e^{j\omega}) \sin^2(2\omega) d\omega \text{ is equal to } \underline{\qquad} \end{split}$$

Ans.

(8)

From the definition of DTFT

$$X(e^{j\omega}) = \sum_{n=-\infty}^{\infty} x[n]e^{-j\omega n}$$

$$x[n] = \frac{1}{2\pi} \int_{-\pi}^{\pi} X(e^{j\omega})e^{j\omega n} d\omega$$

$$x[0] = \frac{1}{2\pi} \int_{-\pi}^{\pi} X(e^{j\omega})Y(e^{j\omega})d\omega = \sum_{n=-\infty}^{\infty} x[0]y[0]$$

$$Y(e^{j\omega}) = \sin^{2}(2\omega)$$

$$= \frac{1-\cos 4\omega}{2} = \frac{1}{2} - \frac{1}{4}e^{4j\omega} - \frac{1}{4}e^{-4j\omega}$$

$$y[n] = \frac{1}{2}\delta[n] - \frac{1}{4}\delta[n+4] - \frac{1}{4}\delta[n-4]$$

$$y[n] = \left\{ -\frac{1}{4}, 0, 0, 0, \frac{1}{2}, 0, 0, 0, -\frac{1}{4} \right\}$$

$$y[0] = \frac{1}{2}$$

$$x[n] = \{6, 3, 8, 7, 4\}; x[0] = 8$$

$$\uparrow$$

$$\frac{1}{\pi} \int_{-\pi}^{\pi} X(e^{j\omega})Y(e^{j\omega})d\omega = 2\sum_{n=-\infty}^{\infty} x[0]y[0] = 2 \times 8 \times \frac{1}{2} = 8$$

$$End of Solution$$

**Q.36** Consider a silicon *p*-*n* junction with a uniform acceptor doping concentration of  $10^{17}$  cm<sup>-3</sup> on the p-side and a uniform donor doping concentration of  $10^{16}$  cm<sup>-3</sup> on the *n*-side. No external voltage is applied to the diode. Given: kT/q = 26 mV,  $n_i = 1.5 \times 10^{10}$  cm<sup>-3</sup>,  $\varepsilon_{si} = 12 \varepsilon_0$ ,  $\varepsilon_0 = 8.85 \times 10^{-14}$  F/m, and  $q = 1.6 \times 10^{-19}$  C. The charge per unit junction area (nC cm<sup>-2</sup>) in the depletion region on the *p*-side is \_\_\_\_\_

Ans. (4.83)

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$$\begin{split} V_0 &= V_T ln \frac{N_A N_D}{n_1^2} \\ &= 26 \times 10^{-3} ln \frac{10^{16} \times 10^{17}}{(1.5 \times 10^{10})^2} \\ V_0 &= 0.757 \, \text{V} \\ W &= \sqrt{\frac{2\varepsilon}{q} \left(\frac{1}{N_A} + \frac{1}{N_D}\right) V_0} \\ &= \sqrt{\frac{2 \times 8.854 \times 10^{-16} \times 12}{1.6 \times 10^{-19}} \left[\frac{1}{10^{16}} + \frac{1}{10^{17}}\right] 0.757} \\ W &= 3.3255 \, \mu\text{cm} \\ W_P &= \frac{WN_D}{N_A + N_D} = \frac{3.3255 \times 10^{-6} \times 10^{16}}{10^{16} + 10^{17}} \\ &= 0.3023 \, \mu\text{cm} \\ \text{harge per unit junction area in the depletion layer on p side is} \\ &= qN_A W_P \\ &= 1.6 \times 10^{-19} \times 10^{17} \times 0.3023 \times 10^{-6} \\ &= 4.8368 \, \text{nc/cm}^2 \end{split}$$

**Q.37** Consider an *n*-channel metal oxide semiconductor field effect transistor (MOSFET)

with a gate-to-source voltage of 1.8 V. Assume that  $\frac{W}{L} = 4$  ,

 $\mu_N C_{ox} = 70 \times 10^{-6} AV^{-2}$ , the threshold voltage is 0.3 V, and the channel length modulation parameter is 0.09 V<sup>-1</sup>. In the saturation region, the drain conductance (in micro seimens) is \_\_\_\_\_

Ans. (28.35)

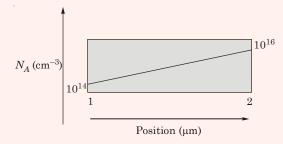
 $\mathbf{C}$ 

In the saturation region

$$\begin{split} g_d &= \lambda I_{DS} \\ &= \lambda \Big[ \frac{1}{2} \mu_n C_{ox} \frac{w}{L} (V_{GS} - V_T)^2 \Big] \\ &= 0.09 \Big[ \frac{1}{2} \times 70 \times 10^{-6} \times 4 (1.8 - 0.3)^2 \Big] \\ g_d &= 28.35 \, \mu s \end{split}$$

End of Solution

**Q.38** The figure below shows the doping distribution in a *p*-type semiconductor in log scale.



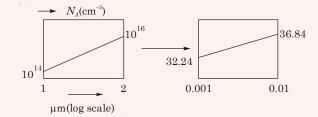
The magnitude of the electric field (in kV/cm) in the semiconductor due to non uniform doping is  $\_\_\_$ 

Ans. (0.0133)

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J = 0

Applying the current density equation

$$J = J_{\text{Drift}} + J_{\text{Diffusion}}$$

∴ There is no net flow of current thus hence, for holes we can write

$$0 = -qD_P \frac{dP}{dx} + q\mu_P PE$$

$$qD_{P} \frac{dP}{dx} = q\mu_{P}PE$$

$$\mu_{P}V_{T} = \mu_{P}PE$$

$$E = \frac{V_{T}}{P}\frac{dP}{dx} \qquad P \cong N_{A}$$

$$E = \frac{V_{T}}{N_{A}}\frac{dN_{A}}{dx}$$

$$E = V_{T}\frac{d}{dx}ln[N_{A}(x)]$$

 $\Rightarrow$ 

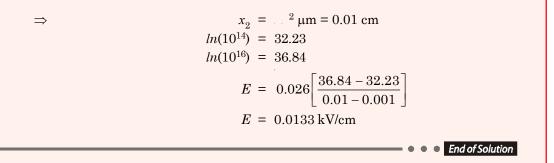
 $\Rightarrow$  now since in the question it is mentioned that the units are in log scale, we can write.

$$\Rightarrow \qquad \qquad \log_{10} x_1 = 1 \mu m$$

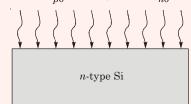
$$x_1 = 10^1 \mu m = 0.001 \text{ cm}$$

$$\log_{10} x_2 = 2 \mu m$$

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**Q.39** Consider a silicon sample at T = 300 K, with a uniform donor density  $N_d = 5 \times 10^{16} \text{ cm}^{-3}$ , illuminated uniformly such that the optical generation rate is  $G_{\text{opt}} = 1.5 \times 10^{20} \text{ cm}^{-3} \text{ s}^{-1}$  throughout the sample. The incident radiation is turned off at t = 0. Assume low-level injection to be valid and ignore surface effects. The carrier lifetimes are  $\tau_{p0} = 0.1 \text{ } \mu \text{s}$  and  $\tau_{n0} = 0.5 \text{ } \mu \text{s}$ .



The hole concentration at t = 0 and the hole concentration at  $t = 0.3 \ \mu s$ , respectively, are

(a)  $1.5 \times 10^{13} \,\mathrm{cm}^{-3}$  and  $7.47 \times 10^{11} \,\mathrm{cm}^{-3}$ 

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- (b)  $1.5 \times 10^{13} \,\mathrm{cm}^{-3}$  and  $8.23 \times 10^{11} \,\mathrm{cm}^{-3}$
- (c)  $7.5 \times 10^{13} \text{ cm}^{-3}$  and  $3.73 \times 10^{11} \text{ cm}^{-3}$
- (d)  $7.5 \times 10^{13} \text{ cm}^{-3} \text{ and } 4.12 \times 10^{11} \text{ cm}^{-3}$
- Ans.

Given

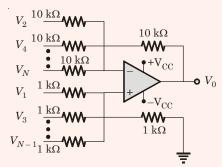
(a)

*.*..

$$\begin{split} G_{\rm opt} &= 1.5 \times 10^{20} / \, {\rm cm}^3 / {\rm sec} \\ G_{\rm opt} &= R = \frac{N_A}{\tau_P} \Rightarrow 1.5 \times 10^{20} = \frac{N_A}{0.1 \times 10^{-6}} \\ N_A &= 1.5 \times 10^{13} / {\rm cm}^3 \\ P(t) &= P_{n0} e^{-t/\tau_P} \\ &= 1.5 \times 10^{13} \ e^{\frac{-0.3}{0.1}} \\ &= 7.46 \times 10^{11} / {\rm cm}^3 \end{split}$$

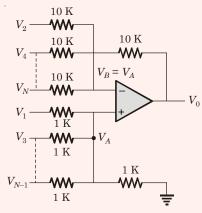
**Q.40** An ideal opamp has voltage sources,  $V_1$ ,  $V_3$ ,  $V_5$ , ...,  $V_{N-1}$  connected to the noninverting input and  $V_2$ ,  $V_4$ ,  $V_6$ , ...,  $V_N$  connected to the inverting input as shown in the figure below (+ $V_{CC}$  = 15 volt, - $V_{CC}$  = -15 volt). The voltages  $V_1$ ,  $V_2$ ,  $V_3$ ,  $V_4$ ,  $V_5$ ,  $V_6$ , ... are 1, -1/2, 1/3, -1/4, 1/5, -1/6, ... volt, respectively. As N approaches infinity, the output voltage (in volt) is \_\_\_\_\_

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Ans. (15)

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Node A:  

$$\frac{V_A - V_1}{1 \text{ K}} + \frac{V_A - V_3}{1 \text{ K}} + \dots \frac{V_A - V_{N-1}}{1 \text{ K}} + \frac{V_A}{1 \text{ K}} = 0$$

$$V_A \left(\frac{N}{2} + 1\right) = V_1 + V_3 + \dots + V_{N-1}$$

$$V_B = V_A \qquad \qquad \because \text{ Virtual short}$$

Node B:

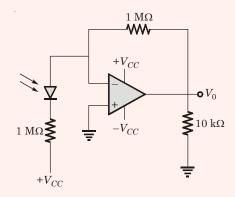
$$\begin{split} \frac{V_A - V_2}{10 \text{ K}} + \frac{V_A - V_4}{10 \text{ K}} + \dots + \frac{V_A - V_N}{10 \text{ K}} + \frac{V_A - V_0}{10 \text{ K}} &= 0 \\ V_0 &= V_A \left(\frac{N}{2} + 1\right) - (V_2 + V_4 + V_6 + \dots + V_N) \\ &= \left(\frac{N}{2} + 1\right) \cdot \frac{(V_1 + V_3 + \dots + V_{N-1})}{\left(\frac{N}{2} + 1\right)} - (V_2 + V_4 + \dots + V_N) \\ &= V_1 - V_2 + V_3 - V_4 + \dots \\ &= 1 + \frac{1}{2} + \frac{1}{3} + \frac{1}{4} \dots = \Sigma \frac{1}{N} = \infty \end{split}$$
  

$$\Rightarrow \text{Output of opamp goes to saturation} \\ V_0 &= V_{\text{sat}} = V_{CC} \end{split}$$

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- **Q.41** A *p-i-n* photodiode of responsivity 0.8 A/W is connected to the inverting input of an ideal opamp as shown in the figure,  $+V_{CC} = 15$  V,  $-V_{CC} = -15$  V, Load resistor  $R_L = 10$  k $\Omega$ . If 10  $\mu$ W of power is incident on the photodiode, then the value of the photocurrent (in  $\mu$ A) through the load is \_\_\_\_\_

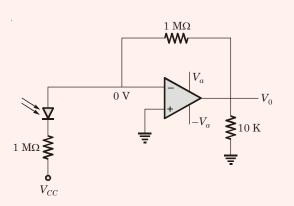


Ans. (800)

 $\Rightarrow$ 

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$$\begin{split} \text{Responsivity} &= \frac{\text{Generated photo current}}{\text{Incident light power}} = \frac{I_0}{P_i} \\ 0.8 \,\text{A/w} &= \frac{I_0}{10 \times 10^{-6}} \\ I_0 &= 8 \,\text{MA} \\ V_0 &= I_0 \times 1 \,\text{M}\Omega = 8 \times 10^{-6} \times 1 \times 10^6 = 8 \,\text{V} \end{split}$$

The photo current through load  $R_L = 10 \text{ k}\Omega$  is given by

$$I_L = \frac{V_0}{R_L} = \frac{8}{10 \times 10^3} = 800 \,\mu\text{A}$$
 (in upward direction)

• • End of Solution

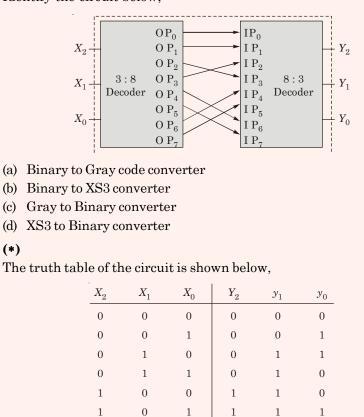
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Q.42 Identify the circuit below,

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Ans.



0

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As per the truth table, none of the options given in the question are correct. However, by making some (minor) changes in the circuit, the answer could be obtained as option (a)

1

1

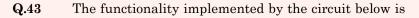
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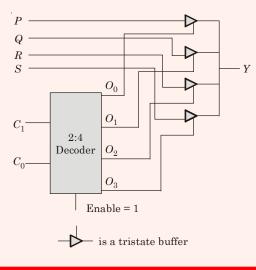


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#### GATE-2016 Exam Solutions Electronics Engg. (Session-1, Set-1)

(a) 2-to-1 multiplexer

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(c) 7-to-1 multiplexer

- (b) 4-to-1 multiplexer
- (d) 6-to-1 multiplexer

#### Ans. (b)

When the outputs  $(O_0, O_1, O_2, O_3)$  of the decoder are at logic 1, the corresponding tristate buffer is activated. In that case, whatever data is applied at the input of a buffer, becomes its output.

Hence, when

*.*..

*.*..

*.*..

*.* .

 $C_1 C_0 = 00,$ Then  $O_0 = 1$ ,  $\Rightarrow$ Y = P $C_1 C_0 = 01,$ Then  $O_1 = 1$ ,  $\Rightarrow$ Y = QThen  $O_2 = 1$ ,  $C_1 C_0 = 10,$  $\Rightarrow$ Y = R $C_1 C_0 = 11,$ Then  $O_3 = 1$ ,  $\Rightarrow$ Y = S

.... the circuit effectively behaves as a 4 to 1 multiplexer.

End of Solution

- **Q.44** In an 8085 system, a PUSH operation requires more clock cycles than a POP operation. Which one of the following options is the correct reason for this?
  - (a) For POP, the data transceivers remain in the same direction as for instruction fetch (memory to processor), whereas for PUSH their direction has to be reversed.
  - (b) Memory write operations are slower than memory read operations in an 8085 based system.
  - (c) The stack pointer needs to be pre-decremented before writing registers in a PUSH, whereas a POP operation uses the address already in the stack pointer.
  - (d) Order of registers has to be interchanged for a PUSH operation, whereas POP uses their natural order.

#### Ans. (c)

For PUSH  $R_p$  instruction in 8085 machine cycles are Fetch(F), Write (W) and Write (W) i.e. 6 + 3 + 3 = 12 T -states/clock cycles. Stack pointer holds the address of previously stored temporary data, so to store new data SP is decremented by '1' after decoding on code, hence fetch has 6T-states unlike 4T - states for most of the instruction.

But for POP  $R_P \rightarrow$  Fetch(F), Read (R) and Read (R) i.e.  $4 + 3 + 3 \rightarrow 10$  T - States

End of Solution

Q.45 The open-loop transfer function of a unity-feedback control system is

$$G(s) = \frac{K}{s^2 + 5s + 5}$$

The value of K at the breakaway point of the feedback control system's root-locus plot is \_\_\_\_\_.

Ans. (1.25)

Characteristic equation is 1 + G(s) H(s) = 0

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$$1 + \frac{K}{s^2 + 5s + 5} = 0$$
  
$$K = -s^2 - 5s - 5$$

For break away point  $\frac{dK}{ds} = 0$ 

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$$\frac{dK}{ds} = -2s - 5 = 0 \Rightarrow s = -2.5$$

Acc. to magnitude condition,

$$\begin{aligned} |G(s) H(s)|_{s=-2.5} &= 1\\ |G(s) H(s)|_{s=-2.5} &= \frac{K}{|(-2.5)^2 + 5 \times -2.5 + 5|} = 1\\ K &= |(6.25 + 5 - 12.5)|\\ K &= 1.25 \end{aligned}$$

End of Solution

**Q.46** The open-loop transfer function of unity-feedback control system is given by

$$G(s) = \frac{K}{s(s+2)}$$

For the peak overshoot of the closed-loop system to a unit step input to be 10%, the value of K is \_\_\_\_\_

Ans. (2.8)

 $\Rightarrow$ 

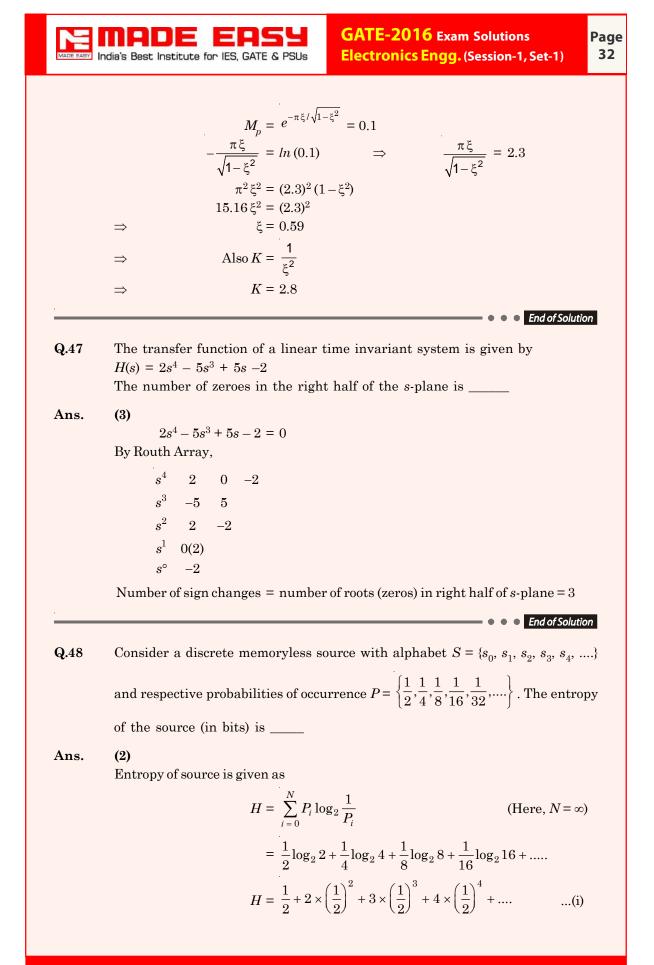
$$G(s) = \frac{K}{s(s+2)}$$
;  $H(s) = 1$ 

Characteristic equation = 1 + G(s) H(s) = 0

$$1 + \frac{K}{s(s+2)} = 0$$
$$s^{2} + 2s + K = 0$$
$$\omega_{n} = \sqrt{K}$$

 $\Rightarrow$ 

$$2\xi\omega_n = 2$$
$$\xi = \frac{1}{\sqrt{K}}$$



 $= \sum_{k=0}^{\infty} k \left(\frac{1}{2}\right)^{k}$   $\frac{H}{2} = \left(\frac{1}{2}\right)^{2} + 2 \times \left(\frac{1}{2}\right)^{3} + 3 \times \left(\frac{1}{2}\right)^{4} + \dots \qquad \dots (ii)$ Subtracting (ii) from (i)  $\frac{H}{2} = \left(\frac{1}{2}\right) + \left(\frac{1}{2}\right)^{2} + \left(\frac{1}{2}\right)^{3} + \dots$   $\frac{H}{2} = \frac{\left(\frac{1}{2}\right)}{1 - \left(\frac{1}{2}\right)} = 1$   $\Rightarrow \qquad H = 2 \text{ bits/symbol}$ End of Solution

**Q.49** A digital communication system uses a repetition code for channel encoding/ decoding. During transmission, each bit is repeated three times (0 is transmitted as 000, and 1 is transmitted as 111). It is assumed that the source puts out symbols independently and with equal probability. The decoder operates as follows: In a block of three received bits, if the number of zeros exceeds the number of ones, the decoder decides in favor of a 0, and if the number of ones exceeds the number of zeros, the decoder decides in favor of a 1. Assuming a binary symmetric channel with crossover probability p = 0.1. The average probability of error is \_\_\_\_\_.

#### Ans. (0.028)

**H** 

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Crossover probability, P = 0.1Average probability of error  $= 3p^2 - 3p^3$  $= 3(0.1)^2 - 2(0.1)^3 = 0.028$ 

• • End of Solution

**Q.50** An analog pulse s(t) is transmitted over an additive white Gaussian noise (A WGN) channel. The received signal is r(t) = s(t) + n(t) where n(t) is additive

white Gaussian noise with power spectral density  $\frac{N_0}{2}$ . The received signal is

h(t). Let  $E_s$  and  $E_h$  denote the energies of the pulse s(t) and the filter h(t), respectively. When the signal to noise ratio (SNR) is maximized at the output of the filter (SNR<sub>max</sub>), which of the following holds?

(a) 
$$E_s = E_h$$
;  $SNR_{max} = \frac{2E_s}{N_0}$  (b)  $E_s = E_h$ ;  $SNR_{max} = \frac{E_s}{2N_0}$   
(c)  $E_s > E_h$ ;  $SNR_{max} > \frac{2E_s}{N_0}$  (d)  $E_s < E_h$ ;  $SNR_{max} = \frac{2E_h}{N_0}$ 

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End of Solution

Ans.

(a)

When the signal to Noise ratio is maximum h(t) = s(T-t)but shifting doesn't change the energy  $\Rightarrow \qquad E_h = E_s$ and  $(SNR)_{max} = \frac{2E_s}{N_0}$ 

Q.51 The current density in a medium is given by

$$\vec{J} = rac{400 \sin heta}{2 \pi (r^2 + 4)} \hat{a}_r \ Am^{-2}$$

The total current and the average current density flowing through the portion of a spherical surface r = 0.8 m,  $\frac{\pi}{12} \le \theta \le \frac{\pi}{4}$ ,  $0 \le \phi \le 2\pi$  are given, respectively, by (a) 15.09 A, 12.86 Am<sup>-2</sup> (b) 18.73 A, 13.65 Am<sup>-2</sup> (c) 12.86 A, 9.23 Am<sup>-2</sup> (d) 10.28 A, 7.56 Am<sup>-2</sup>

Ans. (d)

$$I = \int J \cdot ds$$
  
=  $\int_{\theta=\frac{\pi}{12}}^{\pi/4} \int_{\phi=0}^{2\pi} \frac{400\sin\theta}{2\pi(r^2+4)} \cdot r^2 \sin\theta d\theta d\phi$   
=  $\frac{400}{2\pi(r^2+4)} \cdot r^2 \cdot \phi \Big|_0^{2\pi} \int_{\pi/12}^{\pi/4} \sin^2\theta d\theta$   
=  $\frac{400r^2}{(r^2+4)} \int_{\pi/12}^{\pi/4} \left(\frac{1-\cos 2\theta}{2}\right) d\theta$   
=  $\frac{400 \cdot r^2}{(r^2+4)} \left(\frac{\left(\frac{\pi}{4} - \frac{\pi}{12}\right)}{2} - \left(\frac{\sin 2\theta}{4}\right)_{\pi/12}^{\pi/4}\right)$   
=  $\frac{400 \cdot r^2}{(r^2+4)} \left(\frac{\pi}{12} - \left(\frac{1-1/2}{4}\right)\right)\Big|_{r=0.8}$   
=  $\frac{400 \times 0.8 \times 0.8}{4.64} \times 0.13 = 7.56$  Amp  
Total area =  $\int ds = \iint r^2 \sin\theta d\theta d\phi$ 

$$= r^{2} \int_{\theta=\frac{\pi}{12}}^{\pi/4} \sin\theta d\theta \cdot 2\pi = r^{2} \cdot 2\pi \cdot 0.259 \big|_{r=0.8}$$
$$= 0.8^{2} \times 0.5 \times 2\pi \times \frac{1}{4} = 1.041 \text{ m}^{2}$$
Average current =  $\frac{7.56}{1.041} = 7.56 \text{ A/m}^{2}$ Note : Option (d) is the closest option

- Q.52 An antenna pointing in a certain direction has a noise temperature of 50 K. The ambient temperature is 290 K. The antenna is connected to a pre-amplifier that has a noise figure of 2 dB and an available gain of 40 dB over an effective bandwidth of 12 MHz. The effective input noise temperature  $T_{e}$  for the amplifier and the noise power  $P_{a0}$  at the output of the preamplifier, respectively, are
  - (a)  $T_e = 169.36$  K and  $P_{a0} = 3.73 \times 10^{-10}$  W

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- (b)  $T_e$  = 170.8 K and  $P_{a0}$  = 4.56  $\times$  10  $^{-10}\,{\rm W}$
- (c)  $T_e = 182.5$  K and  $P_{a0} = 3.85 \times 10^{-10}$  W (d)  $T_e = 160.62$  K and  $P_{a0} = 4.6 \times 10^{-10}$  W

Ans. (a)

(i)  

$$T_{e} = (F-1)T_{0} = (10^{2/10} - 1)290$$

$$= 169.6 \text{ K}$$
(ii)  

$$N_{i} = k(T_{ant} + T_{e})B$$

$$= 1.38 \times 10^{-23} \times (50 + 169.6) \times 12 \times 10^{6}$$

$$= 3.63 \times 10^{-14} \text{ W}$$

$$N_{o} = N_{i} \times \text{Gain}$$

$$= 3.63 \times 10^{-14} \times 10^{4}$$

$$= 3.63 \times 10^{-10} \text{ W}$$

End of Solution

Q.53 Two lossless X-band horn antennas are separated by a distance of 200 $\lambda$ . The amplitude reflection coefficients at the terminals of the transmitting and receiving antennas are 0.15 and 0.18, respectively. The maximum directivities of the transmitting and receiving antennas (over the isotropic antenna) are 18 dB and 22 dB, respectively. Assuming that the input power in the lossless transmission line connected to the antenna is 2 W, and that the antennas are perfectly aligned and polarization matched, the power (in mW) delivered to the load at the receiver is \_\_\_\_\_

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$$d = 200 \lambda$$

$$TX RX$$

$$|\Gamma_t| = 0.15 |\Gamma_r| = 0.18$$

$$P_t = 2 W P_r = ?$$

$$G_t = 10^{1.8}, G_r = 10^{2.2}$$

$$P_r = \frac{\left(1 - |\Gamma_t|^2\right)\left(1 - |\Gamma_r|^2\right)G_tG_r}{\left(\frac{4\pi d}{\lambda}\right)^2} \cdot P_t$$

$$= \frac{\left(1 - |0.15|^2\right)\left(1 - |0.18|^2\right)10^{1.8} \cdot 10^{2.2}}{\left(\frac{4\pi 200\lambda}{\lambda}\right)^2} \times 2$$

$$= 10^{-3} W = 2.995 \text{ mW} \approx 3 \text{ mW}$$

End of Solution

**Q.54** The electric field of a uniform plane wave travelling along the negative *z* direction is given by the following equation:

$$\vec{E}_w^i = (\hat{a}_x + j\hat{a}_y)E_0e^{jkz}$$

This wave is incident upon a receiving antenna placed at the origin and whose radiated electric field towards the incident wave is given by the following equation:

$$\vec{E}_a = (\hat{a}_x + 2\hat{a}_y)E_I\frac{1}{r}e^{-jkt}$$

The polarization of the incident wave, the polarization of the antenna and losses due to the polarization mismatch are, respectively,

(a) Linear, Circular (clockwise), –5dB

- (b) Circular (clockwise), Linear, -5dB
- (c) Circular (clockwise), Linear, -3dB
- (d) Circular (anticlockwise), Linear, -3dB

#### Ans.

(c)

$$\vec{E}_w^i = (\hat{a}_x + j\hat{a}_y)E_0e^{jkz}$$

 $\Rightarrow$  Wave contains two orthogonal components and Y component leads X component leads by 90° and also wave is travelling in negative Z-direction.

 $\Rightarrow$  Circular (clockwise) polarization

$$\vec{E}_a = (\hat{a}_x + 2\hat{a}_y)E_I\frac{1}{r}e^{-jkr}$$

 $\Rightarrow$  Wave contains two orthogonal components with unequal amplitudes and both are in-phase.

 $\Rightarrow$  Linear polarization.

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		$PLF = \left  \hat{\rho}_{inc} \cdot \hat{\rho}_{ant} \right ^2$
	where	$\hat{\rho}_{inc} = \frac{\hat{a}_x + j\hat{a}_y}{\sqrt{2}}$
		$\hat{\rho}_{ant} = \frac{\hat{a}_x + 2\hat{a}_y}{\sqrt{5}}$
		PLF = $\left \frac{1+j2}{\sqrt{10}}\right ^2 = \frac{5}{10} = \frac{1}{2}$
	⇒	PLF (dB) = $10 \log \frac{1}{2} = -3 \text{ dB}$
		• • End of Solution
Q.55	The far-zone power de	nsity radiated by a helical antenna is approximated as:
	$\vec{W}_{rad} = \vec{W}_{average} \approx \widehat{a_r} C_0$	$\frac{1}{r^2}\cos^4\theta$
		, nsity is symmetrical with respect to $\phi$ and exists only in
	the upper hemisphere (	$0 \le \theta \le \frac{\pi}{2}$ ; $0 \le \phi \le 2\pi$ ; $C_0$ is a constant. The power radiated
		s) and the maximum directivity of antenna, respectively,
	are	
	(a) $1.5 C_0$ , 10 dB (c) $1.256 C_0$ , 12 dB	(b) $1.256 C_0, 10 \text{ dB}$ (d) $1.5 C_0, 12 \text{ dB}$
Ans.	(b)	$(a) 1.5 C_0, 12 ab$
1115.	Power radiate	$d = \int W_{rad} ds$
		$= \int_{\theta=0}^{\pi/2} \int_{\phi=0}^{2\pi} C_0 \frac{1}{r^2} \cos^4 \theta \cdot r^2 \sin \theta d\theta d\phi$
		$= 2\pi \cdot \frac{C_0}{r^2} \cdot r^2 \int_{\theta=0}^{\pi/2} \cos^4 \theta \cdot d(-\cos \theta)$
		$= 2\pi C_0 \left( -\frac{\cos^5 \theta}{5} \right) \Big _0^{\pi/2} = \frac{2\pi}{5} C_0 = 1.256 C_0$
	Directivit	$y = \frac{4\pi \cdot U}{\int W_{rad} \cdot d\Omega}$
		$= \frac{4\pi \cdot C_0 \cdot \cos^4 \theta}{\int\limits_{\theta=0}^{\pi/2} \int\limits_{\phi=0}^{2\pi} C_0 \cdot \cos^4 \theta \cdot \sin \theta d\theta d\phi} = \frac{2\cos^4 \theta}{1/5} = 10\cos^4 \theta$
	Max valu	he = 10
	$\Rightarrow$ max value (in dE	B) = $10\log_{10} = 10 \text{ dB}$
		• • • End of Solution

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